Elektronische Bauelemente

MMDT4944

NPN+NPN

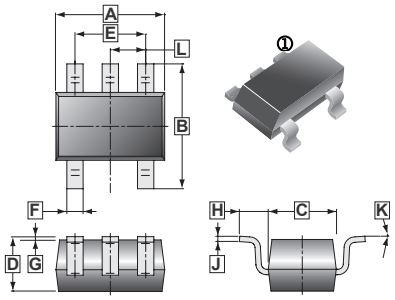
Dual-Chip Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Small package (dual type)
- High voltage and high current
- High h_{FE}, Excellent h_{FE} linearity

SOT-353



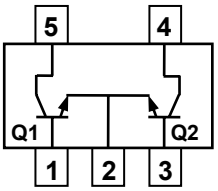
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	G	0.100 REF.	
B	2.15	2.45	H	0.525 REF.	
C	1.15	1.35	J	0.08	0.15
D	0.90	1.10	K	8°	
E	1.20	1.40	L	0.650 TYP.	
F	0.15	0.35			

PACKAGING INFORMATION

Weight: 0.0081g (approximate)

MARKING CODE

LY LGR



ABSOLUTE MAXIMUM RATINGS (at Ta = 25°C unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current – Continuous	I_C	0.15	A
Collector Power Dissipation	Pc	0.20	W
Junction, Storage Temperature	T_J, T_{STG}	+150, -55 ~ +150	℃

ELECTRICAL CHARACTERISTICS (at Ta = 25°C unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	I_C = 100 μA, I_E = 0	$V_{(BR)CBO}$	60	-	-	V
Collector-Emitter Breakdown Voltage	I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	50	-	-	V
Emitter-Base Breakdown Voltage	I_E = 100 μA, I_C = 0	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current	V_{CB} = 60 V, I_E = 0	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current	V_{EB} = 5 V, I_C = 0	I_{EBO}	-		0.1	μA
Collector-Emitter Saturation Voltage	I_C = 100 mA, I_B = 10 mA	$V_{CE(sat)}$	-	-	0.25	V
DC Current Transfer Ratio	V_{CE} = 6V, I_C = 2 mA	h_{FE}	120	-	400	
Transition Frequency	V_{CE} = 10 V, I_C = 1 mA	f_T	80	-	-	MHz
Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1 MHz	C_{OB}	-	-	3.5	pF

CLASSIFICATION OF h_{FE}

Marking	LY	LGR
Rank	Y	GR
Range	120 - 240	200 – 400

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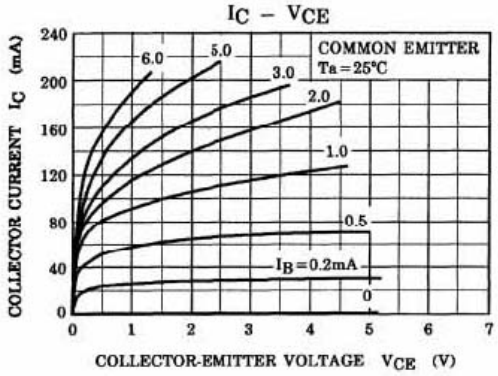
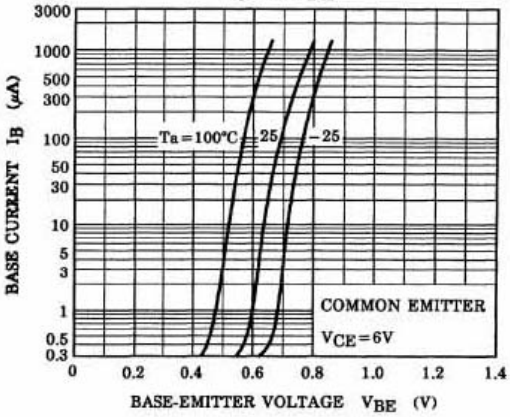
CHARACTERISTIC CURVES

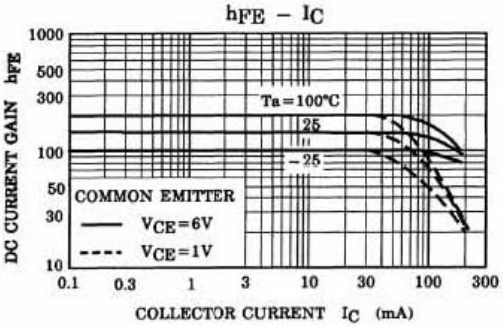
$I_C - V_{CE}$



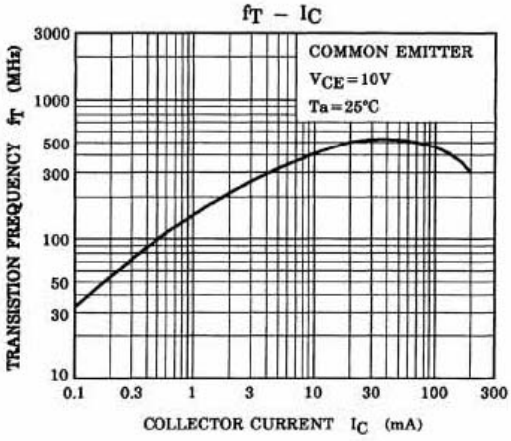
$I_B - V_{BE}$



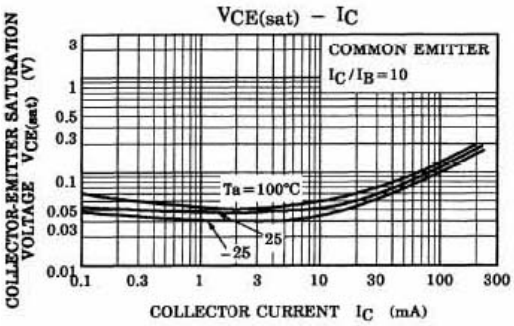
$h_{FE} - I_C$



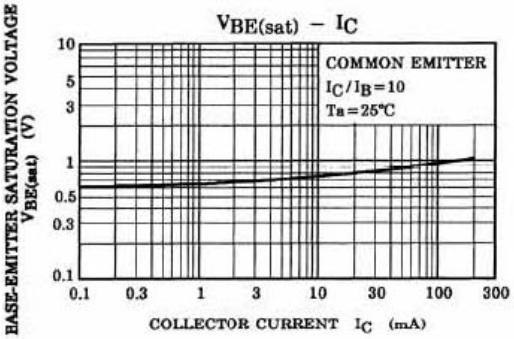
$f_T - I_C$



$V_{CE(sat)} - I_C$



$V_{BE(sat)} - I_C$



$P_C^* - Ta$